# Very Low I<sub>q</sub> LD0 150 mA Regulator with RESET and Delay Time Select

The NCV8660B is a precision very low Iq low dropout voltage regulator. Quiescent currents as low as  $28~\mu A$  typical make it ideal for automotive applications requiring low quiescent current with or without a load. Integrated control features such as Reset and Delay Time Select make it ideal for powering microprocessors.

It is available with a fixed output voltage of 5.0~V and 3.3~V and regulates within  $\pm 2.0\%$ .

#### **Features**

- Fixed Output Voltage of 5 V and 3.3 V
- $\pm 2.0\%$  Output Voltage up to  $V_{BAT} = 40 \text{ V}$
- Output Current up to 150 mA
- Microprocessor Compatible Control Functions:
  - Delay Time Select
  - RESET Output
- NCV Prefix for Automotive
  - Site and Change Control
  - ◆ AEC-Q100 Qualified
- Low Dropout Voltage
- Low Quiescent Current of 28 μA Typical
- Stable Under No Load Conditions
- Protection Features:
  - ◆ Thermal Shutdown
  - ◆ Short Circuit
- These are Pb-Free Devices

#### **Applications**

- Automotive:
  - Body Control Module
  - Instrument and Clusters
  - Occupant Protection and Comfort
  - ♦ Powertrain
- Battery Powered Consumer Electronics

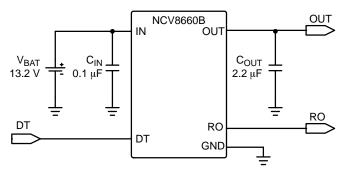
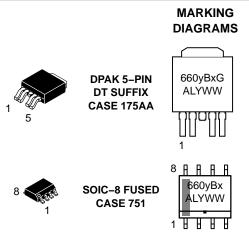


Figure 1. Application Diagram



### ON Semiconductor®

#### www.onsemi.com



= 5 for 5 V Output, 3 for 3.3 V Output

y = 1 for 8 ms, 128 ms Reset Delay,

= 2 for 8 ms, 32 ms Reset Delay

= 3 for 16 ms, 64 ms Reset Delay

= 4 for 32 ms, 128 ms Reset Delay

A = Assembly Location

L = Wafer Lot Y = Year

WW = Work Week

G or = = Pb-Free Package

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the dimensions section on page 12 of this data sheet.

### **PIN DESCRIPTIONS**

Pin				
DPAK	SOIC-8 FUSED	Symbol	Function	
1	1	IN	Input Supply Voltage. 0.1 μF bypass capacitor to GND at the IC.	
2	2	R <sub>O</sub>	Reset Output. CMOS compatible output. Goes low when $\rm V_{OUT}$ drops by more than 7% from nominal.	
3, Tab	5–8	GND	Ground	
4	3	DT	Reset Delay Time Select. Short to GND or connect to OUT to select time.	
5	4	OUT	Regulated Voltage Output. 2.2 μF to ground for typical applications.	

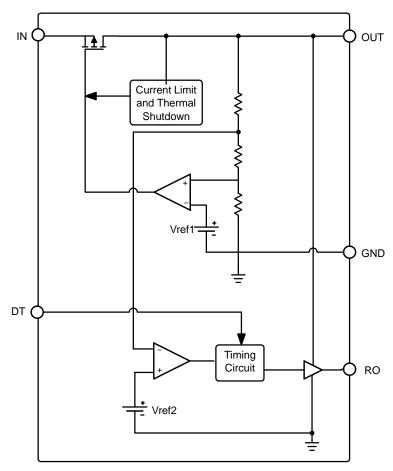


Figure 2. Block Diagram

#### **ABSOLUTE MAXIMUM RATINGS**

Rating		Symbol	Min	Max	Unit
Input Voltage (IN)	$V_{IN}$	-0.3	40	V	
Input Current	I <sub>IN</sub>	-1.0	-	mA	
Output Voltage (OUT) DC Transient, t < 10 s (Note 1)		V <sub>OUT</sub>	-0.3 -0.3	5.5 16	V
Output Current (OUT)		Гоит	-1.0	Current Limited	mA
Storage Temperature Range		T <sub>STG</sub>	-55	150	°C
DT (Reset Delay Time Select) Voltage (Note 2)		$V_{DT}$	-0.3	16	V
DT (Reset Delay Time Select) Current (Note 2)		I <sub>DT</sub>	-1.0	1.0	mA
RO (Reset Output) Voltage DC Transient, t < 10 s		V <sub>RO</sub>	-0.3 -0.3	5.5 16	V
RO (Reset Output) Current		I <sub>RO</sub>	-1.0	1.0	mA
ESD CAPABILITY					•
ESD Capability, Human Body Model (Note 3)		ESD <sub>HB</sub>	-2.0	2.0	kV
ESD Capability, Machine Model (Note 3)		ESD <sub>MM</sub>	-200	200	V
ESD Capability, Charged Device Model (Note 3)		ESD <sub>CDM</sub>	-1.0	1.0	kV
THERMAL RESISTANCE					
Junction-to-Case (Note 4)	DPAK 5	$R_{ heta JC}$		15	°C/W
Junction-to-Ambient (Note 4)	DPAK 5	$R_{ hetaJA}$	66		°C/W
Junction-to-Tab (Note 4)	DPAK 5	$R_{ hetaJT}$	4.0		°C/W
Junction-to-Ambient (Note 4)	SOIC-8 FUSED	$R_{ hetaJA}$	104		°C/W
Junction-to-Lead (pin 6) (Note 4)	$R_{ hetaJT}$	33		°C/W	
LEAD SOLDERING TEMPERATURE AND MSL		•			-
Moisture Sensitivity Level	MSL		1 3	_	
Lead Temperature Soldering: SMD style only, Reflow Pb–Free Part 60 – 150 sec above 217°C, 40 sec ma	SLD	-	265 peak	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. The output voltage must not exceed the input voltage.
- 2. External resistor required to minimize current to less than 1 mA when the control voltage is above 16 V.
- 3. This device series incorporates ESD protection and is tested by the following methods: ESD HBM tested per AEC-Q100-002 (EIA/JESD22-A114)

ESD MM tested per AEC-Q100-003 (EIA/JESD22-A115)

- ESD CDM tested per EIA/JESD22/C101, Field Induced Charge Model
- 4. Values represented typical steady-state thermal performance on 1 oz. copper FR4 PCB with 1 in<sup>2</sup> copper area.
- 5. Per IPC / JEDEC J-STD-020C.

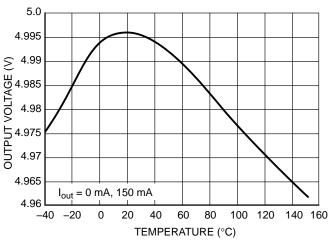
#### **OPERATING RANGE**

Pin Symbol, Parameter	Symbol	Min	Max	Unit
V <sub>IN</sub> , Input Voltage Operating Range	V <sub>IN</sub>	4.5	40	V
Junction Temperature Range	TJ	-40	150	°C

### **ELECTRICAL CHARACTERISTICS** 5.5 V < $V_{IN}$ < 40 V, $-40^{\circ}C \le T_{J} \le +150^{\circ}C$ , unless otherwise specified

Characteristic	Symbol	Conditions	Min	Тур	Max	Unit	
GENERAL				•	•		
Quiescent Current	Iq	$100\mu$ A < $I_{OUT}$ < $150$ mA, $V_{IN}$ = $13.2$ V, $T_{J}$ = $25$ °C	_	25	30	μΑ	
		$100\mu A < I_{OUT} < 150mA, V_{IN} = 13.2V, T_J \le 85$ °C	_	-	40		
Thermal Shutdown (Note 6)	T <sub>SD</sub>		150	175	195	°C	
Thermal Hysteresis (Note 6)	T <sub>HYS</sub>		_	25	-	°C	
OUT							
Output Voltage	V <sub>OUT</sub>	$6 \text{ V} \le \text{V}_{\text{IN}} \le 16 \text{ V}, 0.1 \text{ mA} \le \text{I}_{\text{OUT}} \le 150 \text{ mA}$	4.9	5.0	5.1	V	
		6 V ≤ V <sub>IN</sub> ≤ 40 V, 0.1 mA ≤ I <sub>OUT</sub> ≤ 100 mA	4.9	5.0	5.1		
		$5.6 \text{ V} \le \text{V}_{\text{IN}} \le 16 \text{ V}, 0 \text{ mA} \le \text{I}_{\text{OUT}} \le 150 \text{ mA}, \\ -40^{\circ}\text{C} \le \text{T}_{\text{J}} \le +125^{\circ}\text{C}$	4.9	5.0	5.1		
Output Voltage	V <sub>OUT</sub>	5.5 V ≤ V <sub>IN</sub> ≤ 16 V, 0.1 mA ≤ I <sub>OUT</sub> ≤ 150 mA	3.234	3.3	3.366	V	
		$5.5 \text{ V} \le \text{V}_{\text{IN}} \le 40 \text{ V}, 0.1 \text{ mA} \le \text{I}_{\text{OUT}} \le 100 \text{ mA}$	3.234	3.3	3.366		
Output Current Limit	I <sub>CL</sub>	OUT = 96% x V <sub>OUT</sub> nominal	205	_	525	mA	
Output Current Limit, Short Circuit	I <sub>SCKT</sub>	OUT = 0 V	205	_	525	mA	
Load Regulation	$\Delta V_{OUT}$	V <sub>IN</sub> = 13.2 V, I <sub>OUT</sub> = 0.1 mA to 150 mA	-40	10	40	mV	
Line Regulation	$\Delta V_{OUT}$	I <sub>OUT</sub> = 5 mA, V <sub>IN</sub> = 6 V to 28 V	-20	0	20	mV	
Dropout Voltage – 5.0 V Only	$V_{DR}$	$I_{OUT} = 100 \text{ mA}, \text{ (Note 7)}$ $V_{DR} = V_{IN} - V_{OUT}, \text{ ($\Delta V_{OUT} = -100 mV)}$	-	0.225	0.45	V	
		$I_{OUT}$ = 150 mA, (Note 7) $V_{DR}$ = $V_{IN}$ - $V_{OUT}$ , ( $\Delta V_{OUT}$ = -100 mV)	-	0.30	0.60		
Output Load Capacitance	CO	Output capacitance for stability	2.2	-	-	μF	
Power Supply Ripple Rejection	PSRR	V <sub>IN</sub> = 13.2 V, 0.5 V <sub>PP</sub> , 100 Hz	_	60	_	dB	
DT (Reset Delay Time Select)				•	•		
Threshold Voltage High			2	_	_	V	
Low			_	-	0.8	V	
Input Current		$DT = V_{OUT}$	_	-	1.0	μΑ	
RO, Reset Output							
RESET Threshold	$V_{Rf}$	V <sub>OUT</sub> decreasing	90	93	96	%V <sub>OUT</sub>	
RESET Threshold Hysteresis	$V_{Rhys}$		-	2.0	_	%V <sub>OUT</sub>	
RO Output Low	$V_{RL}$	10 kΩ RESET to OUT, $V_{OUT} = 4.5 \text{ V}$	_	0.2	0.4	<b>V</b>	
RO Output High (OUT-RO)	V <sub>RH</sub>	10 kΩ RESET to GND	V <sub>OUT</sub> -0.4	V <sub>OUT</sub> -0.2	V <sub>OUT</sub>	٧	
Reset Reaction Time	t <sub>RR</sub>	V <sub>OUT</sub> into UV to RESET Low	16	25	38	μsec	
Input Voltage Reset Threshold	V <sub>IN_RT</sub>	V <sub>IN</sub> Decreasing, V <sub>OUT</sub> > V <sub>RT</sub>	_	3.8	4.25	V	
RESET Delay with DT Selection							
Delay Time Out of RESET  - 8 ms version  - 16 ms version  - 32 ms version  - 64 ms version  - 128 ms version	t <sub>dRx</sub>	V <sub>OUT</sub> into regulation to RO High	5.0 10 20 40 80	8.0 16 32 64 128	11.5 23 46 92 184	msec	

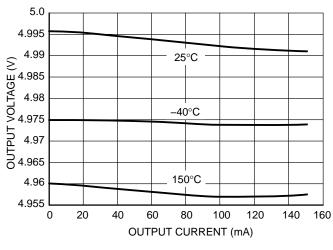
<sup>6.</sup> Not production tested, guaranteed by design.
7. Dropout at a given current level is defined as the voltage difference of V<sub>IN</sub> to V<sub>OUT</sub> with V<sub>IN</sub> decreasing until the output drops by 100 mV.



3.315 3.310 3.305 € 3.300 **OUTPUT VOLTAGE** 3.295 3.290 3.285 3.280 3.275 3.270  $I_{out} = 0 \text{ mA}, 150 \text{ mA}$ 3.265 3.260 -40 -20 20 40 60 80 100 120 TEMPERATURE (°C)

Figure 3. Output Voltage vs. Temperature (OUT = 5 V)

Figure 4. Output Voltage vs. Temperature (OUT = 3.3 V)



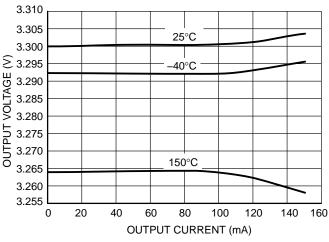
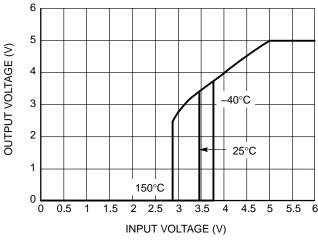


Figure 5. Output Voltage vs. Output Current (OUT = 5 V)

Figure 6. Output Voltage vs. Output Current (OUT = 3.3 V)



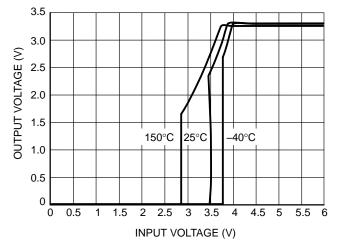
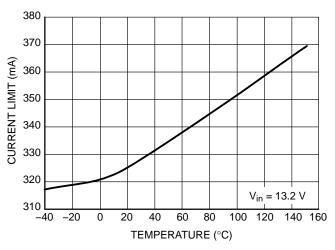


Figure 7. Output Voltage vs. Input Voltage  $(R_{LOAD} = 51 \text{ k, } I_{out} = 100 \mu\text{A, OUT} = 5 \text{ V})$ 

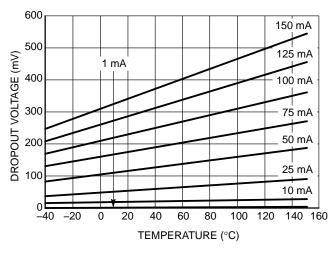
Figure 8. Output Voltage vs. Input Voltage  $(R_{LOAD} = 33 \text{ k}, I_{out} = 100 \mu\text{A}, OUT = 3.3 \text{ V})$ 



600 500 DROPOUT VOLTAGE (mV) 400 150°C 300 25°C 200 100 -40°C 25 50 75 100 125 0 150 **OUTPUT CURRENT (mA)** 

Figure 9. Current Limit vs. Temperature

Figure 10. Dropout Voltage vs. Output Current



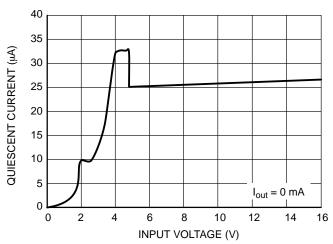
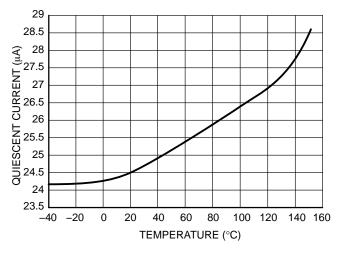


Figure 11. Dropout Voltage vs. Temperature

Figure 12. Quiescent Current vs. Input Voltage



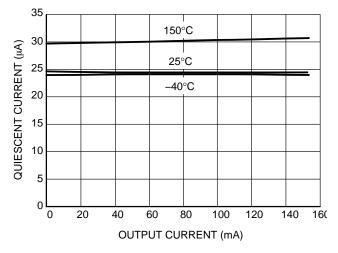


Figure 13. Quiescent Current vs. Temperature

Figure 14. Quiescent Current vs. Output Current

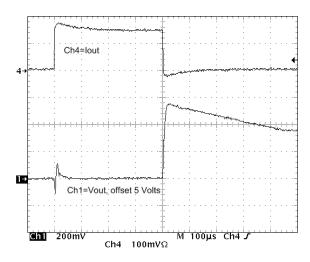


Figure 15. Load Transient (V<sub>IN</sub> = 13.2 V, OUT = 5 V)

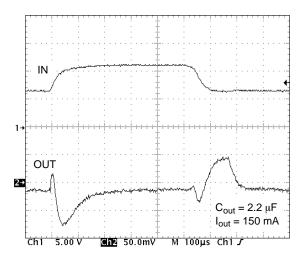


Figure 16. Line Transient (OUT = 5 V)

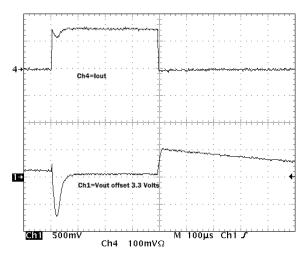


Figure 17. Load Transient (V<sub>IN</sub> = 13.2 V, OUT = 3.3 V)

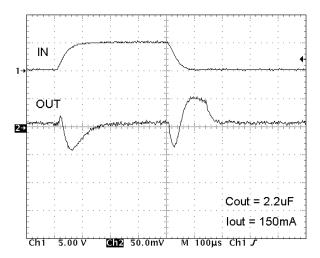
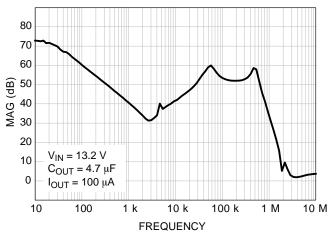


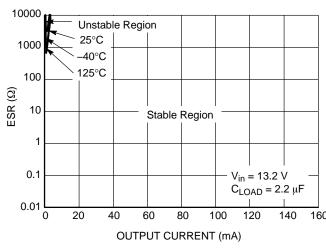
Figure 18. Line Transient (OUT = 3.3 V)



80 70 60 (db) 20 40 30 30 20  $V_{IN} = 13.2 \text{ V}$ 10  $C_{OUT} = 4.7 \mu F$  $I_{OUT} = 150 \text{ mA}$ 100 k 10 100 1 k 10 k 1 M 10 M **FREQUENCY** 

Figure 19. Ripple Rejection vs. Frequency ( $V_{IN}$  = 13.2 V,  $I_{OUT}$  = 100  $\mu$ A)

Figure 20. Ripple Rejection vs. Frequency (V<sub>IN</sub> = 13.2 V, I<sub>OUT</sub> = 150 mA)



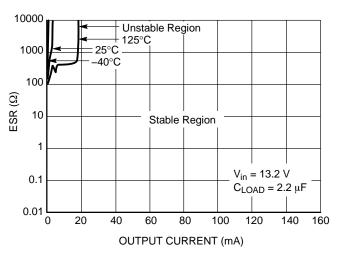


Figure 21. Output Capacitor ESR vs. Output Current (OUT = 5 V)

Figure 22. Output Capacitor ESR vs. Output Current (OUT = 3.3 V)

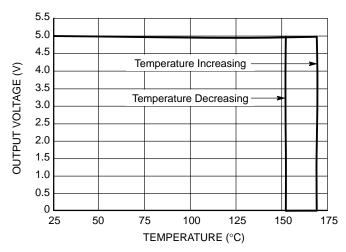


Figure 23. Thermal Shutdown vs. Temperature

#### **DETAILED OPERATING DESCRIPTION**

#### General

The NCV8660B is a 5 V and 3.3 V linear regulator providing low drop—out voltage for 150 mA at low quiescent current levels. Also featured in this part is a reset output with selectable delay times. Delay times are selectable via part selection and control through the Delay Time Select (DT) pin. No pull—up resistor is needed on the reset output (RO). Pull—up and pull—down capability are included. Only a small bypass capacitor on the input (IN) supply pin and output (OUT) voltage pin are required for normal operation. Thermal shutdown functionality protects the IC from damage caused from excessively high temperatures appearing on the IC.

#### **Output Voltage**

Output stability is determined by the capacitor selected from OUT to GND. The NCV8660B has been designed to work with low ESR (equivalent series resistance) ceramic capacitors. The device is extremely stable using virtually any capacitor 2.2  $\mu F$  and above. Reference the Output Capacitor Stability graph in Figure 21.

The output capacitor value will affect overshoot during power-up. A lower value capacitor will cause higher overshoot on the output. System evaluation should be performed with minimum loading for evaluation of overshoot.

Selection of process technology for the NCV8660B allows for low quiescent current independent of loading. Quiescent current will remain flat across the entire range of loads providing a low quiescent current condition in standby and under heavy loads. This is highly beneficial to systems requiring microprocessor interrupts during standby mode as duty cycle and load changes have no impact on the standby current. Reference Figure 14 for Quiescent Current vs Output Current.

#### **Current Limit**

Current limit is provided on OUT to protect the IC. The minimum specification is 205 mA. Current limit is specified under two conditions (OUT = 96% x OUT nominal) and (OUT = 0 V). No fold–back circuitry exists. Any measured differences can be attributed to change in die temperature. The part may be operated up to 205 mA provided thermal die temperature is considered and is kept below  $150^{\circ}$ C. Degradation of electrical parameters at this current is expected at these elevated levels. A reset (RO) will not occur with a load less than 205 mA.

#### **Reset Output**

A reset signal is provided on the Reset Output (RO) pin to provide feedback to the microprocessor of an out of regulation condition. This is in the form of a logic signal on RO. Output (OUT) voltage conditions below the RESET threshold cause RO to go low. The RO integrity is maintained down to OUT = 1.0 V.

The Reset Output (RO) circuitry includes an active internal pullup to the output (OUT) as shown in Figure 24. No external pullup is neccessary.

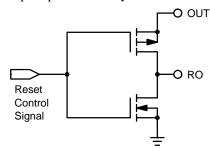


Figure 24. Reset Output Circuitry

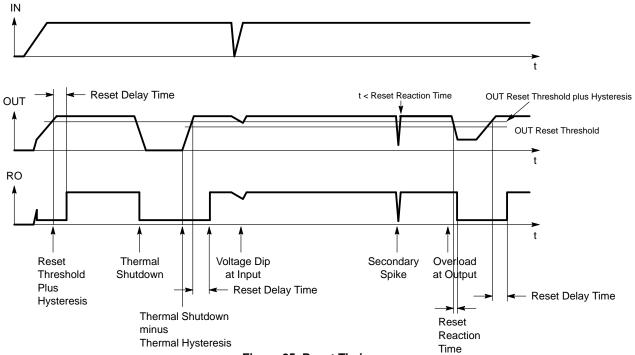


Figure 25. Reset Timing

During power-up (or restoring OUT voltage from a reset event), the OUT voltage must be maintained above the Reset threshold for the Reset Delay time before RO goes high. The time for Reset Delay is determined by the choice of IC and the state of the DT pin.

### **Reset Delay Time Select**

Selection of the NCV8660B device and the state of the DT pin determines the available Reset Delay times. The part is designed for use with DT tied to ground or OUT, but may be controlled by any logic signal which provides a threshold between 0.8 V and 2 V. The default condition for an open DT pin is the slower Reset time (DT = GND condition). Times are in pairs and are highlighted in the chart below. Consult factory for availability.

	DT=GND	DT=OUT
	Reset Time	Reset Time
NCV86601B	8 ms	128 ms
NCV86602B	8 ms	32 ms
NCV86603B	16 ms	64 ms
NCV86604B	32 ms	128 ms

The Delay Time select (DT) pin is logic level controlled and provides Reset Delay time per the chart. Note the DT pin is sampled only when RO is low, and changes to the DT pin when RO is high will not effect the reset delay time.

#### **Thermal Shutdown**

When the die temperature exceeds the Thermal Shutdown threshold, a Thermal Shutdown event is detected OUT is turned off, and RO goes low. The IC will remain in this state until the die temperature moves below the shutdown threshold (175°C typical) minus the hysteresis factor (25°C typical). The output will then turn back on and RO will go high after the RESET Delay time.

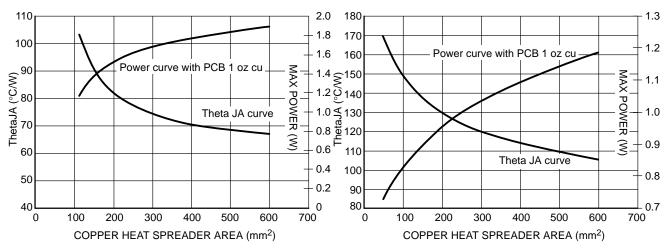


Figure 26.  $R_{\theta JA}$  vs. PCB Copper Area (DPAK)

Figure 28. R<sub>θJA</sub> vs. PCB Copper Area (SOIC–8 Fused)

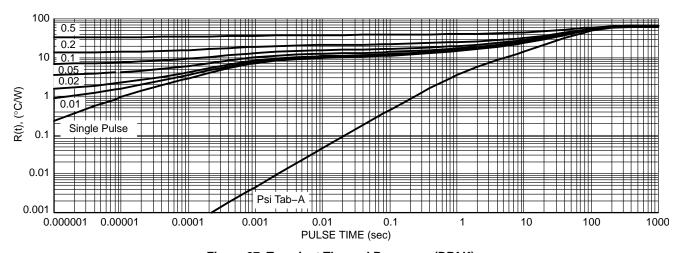


Figure 27. Transient Thermal Response (DPAK)

Cu Area = 645 mm<sup>2</sup>

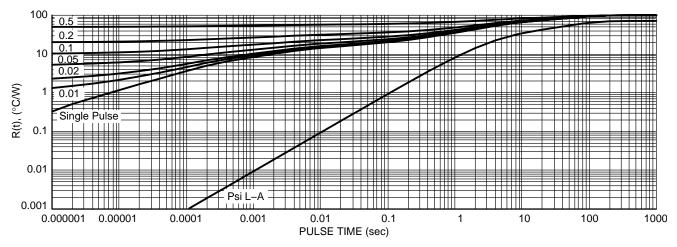


Figure 29. Transient Thermal Response (SOIC-8 Fused)
Cu Area = 645 mm<sup>2</sup>

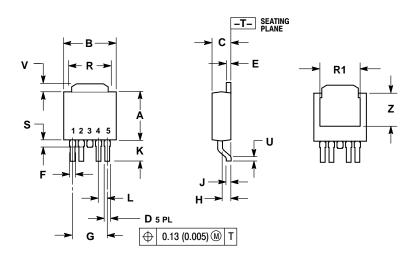
#### **ORDERING INFORMATION**

Device	Output Voltage	Reset Delay Time, DT to GND	Reset Delay Time, DT to OUT	Package	Shipping <sup>†</sup>	
NCV86601BDT50RKG		8 ms	128 ms			
NCV86602BDT50RKG		8 ms	32 ms	DPAK	2500 / Tong & Dool	
NCV86603BDT50RKG		16 ms	64 ms	(Pb-Free)	2500 / Tape & Reel	
NCV86604BDT50RKG	501/	32 ms	128 ms			
NCV86601BD50R2G	5.0 V	8 ms	128 ms		2500 / Tape & Reel	
NCV86602BD50R2G		8 ms	32 ms	SOIC-8 FUSED (Pb-Free)		
NCV86603BD50R2G		16 ms	64 ms			
NCV86604BD50R2G		32 ms	128 ms			
NCV86601BDT33RKG		8 ms	128 ms			
NCV86602BDT33RKG		8 ms	32 ms	DPAK	0500 / Tana 8 Daal	
NCV86603BDT33RKG		16 ms	64 ms	(Pb-Free)	2500 / Tape & Reel	
NCV86604BDT33RKG	22.1/	32 ms	128 ms			
NCV86601BD33R2G	3.3 V	8 ms	128 ms			
NCV86602BD33R2G		8 ms	32 ms	SOIC-8 FUSED	2500 / Tone 9 Deal	
NCV86603BD33R2G		16 ms	64 ms	(Pb-Free)	2500 / Tape & Reel	
NCV86604BD33R2G		32 ms	128 ms			

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### **PACKAGE DIMENSIONS**

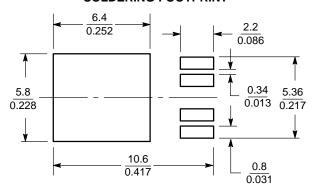
#### **DPAK 5, CENTER LEAD CROP** CASE 175AA **ISSUE B**



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.020	0.028	0.51	0.71
Е	0.018	0.023	0.46	0.58
F	0.024	0.032	0.61	0.81
G	0.180 BSC		4.56 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.045	BSC	1.14	BSC
R	0.170	0.190	4.32	4.83
R1	0.185	0.210	4.70	5.33
S	0.025	0.040	0.63	1.01
U	0.020		0.51	
٧	0.035	0.050	0.89	1.27
Z	0.155	0.170	3.93	4.32

#### **SOLDERING FOOTPRINT\***



SCALE 4:1  $\left(\frac{\text{mm}}{\text{inches}}\right)$ 

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

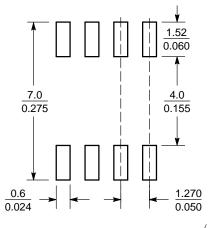
# SOIC-8 NB CASE 751-07 **ISSUE AK** -X-В 0.25 (0.010) M Y M -Y-G С SEATING 0.10 (0.004) 0.25 (0.010) M Z YS X(S)

#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27 BSC		0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### SOLDERING FOOTPRINT\*



SCALE 6:1

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